

**Vishay Semiconductors** 

# Thyristor High Voltage, Surface Mount Phase Control SCR, 16 A



PRIMARY CHARACTERISTICS			
I <sub>T(AV)</sub>	10 A		
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V		
V <sub>TM</sub>	1.4 V		
I <sub>GT</sub>	60 mA		
TJ	-40 °C to 125 °C		
Package	D <sup>2</sup> PAK (TO-263AB)		
Circuit configuration	Single SCR		

## **FEATURES**

J-STD-020, Meets MSL level 1, per LF maximum peak of 245 °C



 Designed and qualified according JEDEC<sup>®</sup>-JESD 47

RoHS COMPLIANT HALOGEN FREE

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **APPLICATIONS**

- Input rectification (soft start)
- · Vishay input diodes, switches and output rectifiers which are available in identical package outlines

### DESCRIPTION

The VS-16TTS..S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS						
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 $\mu m)$ copper	2.5	3.5	2			
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	6.3	9.5	A			
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	14.0	18.5				

### Note

T<sub>A</sub> = 55 °C, T<sub>J</sub> = 125 °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	TEST CONDITIONS	VALUES	UNITS	
I <sub>T(AV)</sub>	Sinusoidal waveform	10	٨	
I <sub>RMS</sub>		16	A	
V <sub>RRM</sub> /V <sub>DRM</sub>		800 to 1200	V	
I <sub>TSM</sub>		200	A	
V <sub>T</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V	
dV/dt		500	V/µs	
dl/dt		150	A/µs	
TJ		-40 to +125	°C	

VOLTAGE RATINGS						
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 ℃ mA			
VS-16TTS08S-M3	800	800	- 10			
VS-16TTS12S-M3	1200	1200	10			

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
FARAMETER	STINDUL	TEST CONDITIONS	TYP. MAX.			
Maximum average on-state current	I <sub>T(AV)</sub>	$T_{C}$ = 98 °C, 180° conduction, half sine wave	10			
Maximum RMS on-state current	I <sub>RMS</sub>		16	Α		
Maximum peak, one-cycle,	<b>I</b>	10 ms sine pulse, rated V <sub>RRM</sub> applied	170	~		
non-repetitive surge current	ITSM	10 ms sine pulse, no voltage reapplied	200			
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	144	A <sup>2</sup> s		
Maximum r-t for fusing	141	10 ms sine pulse, no voltage reapplied	200			
Maximum I <sup>2</sup> $\sqrt{t}$ for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied	2000	A²√s		
Maximum on-state voltage drop	V <sub>TM</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V		
On-state slope resistance	r <sub>t</sub>	T 105 %O	24.0	mΩ		
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C	1.1	V		
Maximum variance and divect lockage current	1 /1	$T_J = 25 \text{ °C}$ $V_R = \text{rated } V_{RRM} / V_{DRM}$	0.5			
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	10			
Holding current	Ι <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C	- 150	mA		
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J$ = 25 °C	200	]		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max. linear to 80 % $V_{DRM} = R_g - k = open$	500	V/µs		
Maximum rate of rise of turned-on current	dl/dt	15		A/µs		

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P <sub>GM</sub>		8.0	W		
Maximum average gate power	P <sub>G(AV)</sub>		2.0	vv		
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	А		
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V		
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J$ = - 10 °C	90			
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	60	mA		
		Anode supply = 6 V, resistive load, $T_J$ = 125 °C	35			
		Anode supply = 6 V, resistive load, $T_J$ = - 10 °C	3.0			
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	2.0	v		
		Anode supply = 6 V, resistive load, $T_J$ = 125 °C	1.0	v		
Maximum DC gate voltage not to trigger	V <sub>GD</sub>					
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	2.0	mA		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9			
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.1</sub> = 125 °C	4	μs		
Typical turn-off time	t <sub>q</sub>	1J = 125 C	110			



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THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C		
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.3	°C/W		
Typical thermal resistance, junction to ambient	R <sub>thJA</sub>	PCB mount <sup>(1)</sup>	40	C/W		
Approximate weight			2	g		
Approximate weight			0.07	oz.		
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)		08S		
		Case signe D T AIX (TO-200AD)	16TTS12S			

#### Note

(1) When mounted on 1" square (650 mm<sup>2</sup>) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W.

For recommended footprint and soldering techniques refer to application note #AN-994

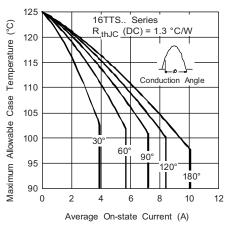


Fig. 1 - Current Rating Characteristics

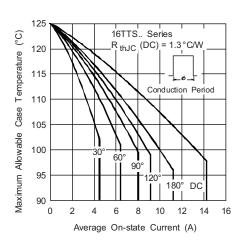


Fig. 2 - Current Rating Characteristics

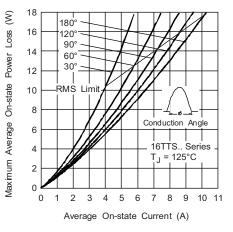


Fig. 3 - On-State Power Loss Characteristics

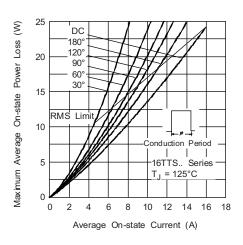


Fig. 4 - On-State Power Loss Characteristics

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## VS-16TTS08S-M3, VS-16TTS12S-M3 Series

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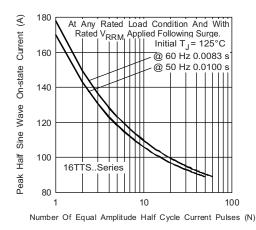


Fig. 5 - Maximum Non-Repetitive Surge Current

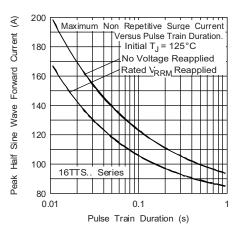


Fig. 6 - Maximum Non-Repetitive Surge Current

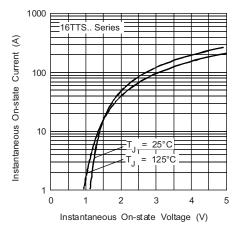
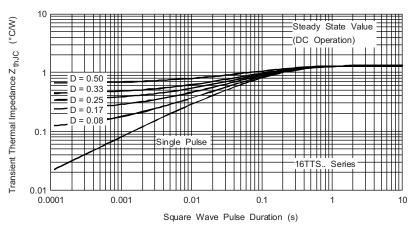


Fig. 7 - On-State Voltage Drop Characteristics



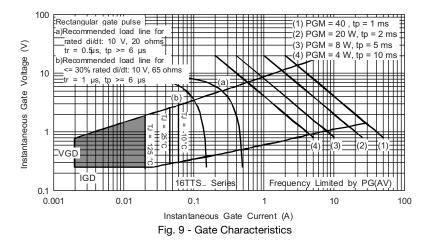


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# VS-16TTS08S-M3, VS-16TTS12S-M3 Series

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### **ORDERING INFORMATION TABLE**

Device code	vs-	16	т	т	s	12	S	TRL	-M3
		(2)	(3)	(4)	(5)	6			(9)
		Vial			toro or	duat	$\bigcirc$	$\bigcirc$	$\bigcirc$
	님 '		•	nicondu	cors pro	Jauci			
	2 -		rent rati	0					
	3			iguration	1:				
			single t	nyristor					
	4 -		kage:	(TO 20)					
				(TO-263	SAB)				
	5 -		e of silio						
				rd recov	-			[	08 = 80
	6 -	· Vol	tage rati	ng: volta	age cod	e x 100	$= V_{RRN}$	1	12 = 12
	7 -	- S =	surface	mounta	able			L	
	8 -	• No	one = tu	be					
		• TF	RL = tap	e and re	el (left d	oriented	I)		
		• TF	RR = tap	be and r	eel (righ	t oriente	ed)		
	9 -	-M3	s = halog	gen-free	, RoHS-	complia	ant, and	termina	ations le

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-16TTS08S-M3	50	1000	Antistatic plastic tubes			
VS-16TTS08STRR-M3	800	800	13" diameter reel			
VS-16TTS08STRL-M3	800	800	13" diameter reel			
VS-16TTS12S-M3	50	1000	Antistatic plastic tubes			
VS-16TTS12STRR-M3	800	800	13" diameter reel			
VS-16TTS12STRL-M3	800	800	13" diameter reel			

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96164			
Part marking information	www.vishay.com/doc?95444			
Packaging information	www.vishay.com/doc?96424			
SPICE model	www.vishay.com/doc?96772			

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D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIMETERS		INCHES		NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES	
A	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

S١	SYMBOL	MILLIMETERS		INCHES		NOTES
	STWBUL	MIN.	MAX.	MIN.	MAX.	NOTES
	D1	6.86	8.00	0.270	0.315	3
	E	9.65	10.67	0.380	0.420	2, 3
	E1	7.90	8.80	0.311	0.346	3
	е	2.54 BSC		0.100 BSC		
	Н	14.61	15.88	0.575	0.625	
	L	1.78	2.79	0.070	0.110	
	L1	-	1.65	-	0.066	3
	L2	1.27	1.78	0.050	0.070	
	L3	0.25 BSC		0.010 BSC		
	L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

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